Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	99	("5319395" "5877742" "5764581" "6072185" "6237122" "6243348" "4796260" "5430861" "5805155" "5845292" "5930518" "6181609" "4313160" "4455483" "4847842" "5255383" "5321699" "5386422" "5388074" "5469444" "5481531" "5524234" "5524235" "5608892" "5684774" "5797027" "5841717" "5860111" "5917429" "6163832" "6178121" "6233668" "4849974" "4849976" "4855903" "4953121" "5274782" "5280584" "5416916" "5469551" "5477492" "5511212" "5537577" "5561671" "5657398" "5664149" "5742509" "5781495" "5809273" "5818789").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 11:00
L2	50	("5319395" "5877742" "5764581" "6072185" "6237122" "6243348" "4796260" "5430861" "5805155" "5845292" "5930518" "6181609" "4313160" "4455483" "4847842" "5255383" "5321699" "5386422" "5388074" "5469444" "5481531" "5524234" "5524235" "5608892" "5684774" "5797027" "5841717" "5860111" "5917429" "6163832" "6178121" "6233668" "4849974" "4849976" "4855903" "4953121" "5274782" "5280584" "5416916" "5469551" "5477492" "5511212" "5537577" "5561671" "5657398" "5664149" "5742509" "5781495" "5809273" "5818789").pn.	USPAT	OR	ON	2006/02/20 11:05
L3	3977	(write and read) same (time adj period)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 11:07
L4	4	l3 and l2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 11:06
L5	1089	(write and read) same (time adj period) same (first)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 11:07

L6	638	(write and read) same (time adj period) same (first and second)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 11:07
L7	8	l6 and (data near2 retention)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 12:11
L8	2913	memory with (data near2 retention)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 12:12
L9	594	(memory with (data near2 retention)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 12:12
L10	536260	(test testing tester tested and (memory with (data near2 retention))).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 12:12
L11	63	((test testing tester tested) and (memory with (data near2 retention))).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 12:12
L12	8	("5034923" | "5255230" | "5361232" | "5428574" | "5491665" | "5733032" | "5936902" | "6378102").PN. OR ("6681350"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 15:38
L13	15	("3655959" | "4093958" | "5132772" | "5222066" | "5241266" | "5361232" | "5519333" | "5570317" | "5654588" | "5949242" | "6067262" | "6167541" | "6175244" | "6208567").PN. OR ("6697978").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 15:44
L14	3	l13 and (data near2 retention)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 17:33

L15	55	("3795859" | "4541090" | "4594711" | "4601034" | "4635261" | "4801870" | "4872168" | "4903266" | "4910735" | "5033048").PN. OR ("5222066"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 17:32
L16	5	l15 and (data near2 retention)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 18:18
L17	18	("5222066" | "5491665" | "5495448" | "5559745" | "5577050" | "5642318").PN. OR ("5835429"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/20 18:17
L18	9	l17 and (data near2 retention)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 18:35
L19	4	"611099"	US-PGPUB; USPAT	OR	ON	2006/02/20 18:36
L20	5	"614642"	US-PGPUB; USPAT	OR	ON	2006/02/20 21:38
L21	7	"6496947"	USPAT	OR	ON	2006/02/20 21:38

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Key: IEEE JNL = IEEE Journal or Magazine, IEE JNL = IEE Journal or Magazine, IEEE CNF = IEEE Conference, IEE CNF = IEE Conference, IEEE STD = IEEE Standard

1. **Mobile ion-induced data retention failure in NOR flash memory cell**
   Lee, W.H.; Dong-Kyu Lee; Keon-Soo Kim; Kun-Ok Ahn; Kang-Deog Suh;
   Device and Materials Reliability, IEEE Transactions on
   Volume 1, Issue 2, June 2001 Page(s):128 - 132
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2. **Enhanced quality of tunnel oxide by in-situ screen oxide for embedded flash memory application**
   Nakamura, T.; Ichii, M.;
   Semiconductor Manufacturing, 2000. Proceedings of ISSM 2000. The Ninth International Symposium on
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3. **The effect of the floating gate/tunnel SiO_2 interface on FLASH memory data retention reliability**
   Kubota, T.; Ando, K.; Muramatsu, S.;
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   30 April-2 May 1996 Page(s):12 - 16
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4. **Block-based multiperiod dynamic memory design for low data-retention power**
   Joohee Kim; Papaefthymiou, M.C.;
   Very Large Scale Integration (VLSI) Systems, IEEE Transactions on
   Volume 11, Issue 6, Dec. 2003 Page(s):1006 - 1018
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5. **Effects of Fowler Nordheim tunneling stress vs. Channel Hot Electron stress on data retention characteristics of floating gate non-volatile memories**
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6. **The mechanical stress effects on data retention reliability of NOR flash memory**
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7. **Data retention characteristics of sub-100 nm NAND flash memory cells**
   Jae-Duk Lee; Jeong-Hyuk Choi; Donggun Park; Kinam Kim;
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8. **Study of data retention for nanocrystal Flash memories**
   Compagnoni, C.M.; Ielmini, D.; Spinelli, A.S.; Lacaita, A.L.; Previtali, C.; Gerardi, C.;
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   30 March-4 April 2003 Page(s):506 - 512
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9. **A forced-voltage technique to test data retention faults in CMOS SRAM by I_{DDQ} testing**
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11. **Low-voltage DRAM sensing scheme with offset-cancellation sense amplifier**
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14. **A new data retention mechanism after endurance stress on flash memory**
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Recent progress in FET-type ferroelectric memories
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21. **Energy-aware memory allocation in heterogeneous non-volatile memory systems**
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23. **Characterization of multi-barrier tunneling diodes and vertical transistors using 2-D device simulation**
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24. **DRG-cache: a data retention gated-ground cache for low power**
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1. **Quick address detection of anomalous memory cells in a flash memory test structure**
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Volume 10, Issue 2, May 1997 Page(s):196 - 200
IEEE JNL

2. **An efficient BIST method for testing of embedded SRAMs**
Tehranipour, M.H.; Navabi, Z.; Fakhraie, S.M.;
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3. **Zero-overhead BIST for internal-SRAM testing**
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4. **Assessing SRAM test coverage for sub-micron CMOS technologies**
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5. **Self-learning signature analysis for non-volatile memory testing**
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Inventor Name Search Result

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Last Name = DIXIT
First Name = CHARUTOSH

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09449324	6542834	150	11/24/1999	CAPACITANCE ESTIMATION	DIXIT, CHARUTOSH
09515250	6484297	150	02/29/2000	4K DERATING SCHEME FOR PROPAGATION DELAY AND SERUP/HOLD TIME COMPUTATION	DIXIT, CHARUTOSH
09727426	6449760	150	11/30/2000	PIN PLACEMENT METHOD FOR INTEGRATED CIRCUITS	DIXIT, CHARUTOSH
10163208	6829754	150	06/04/2002	METHOD AND SYSTEM FOR CHECKING FOR POWER ERRORS IN ASIC DESIGNS	DIXIT, CHARUTOSH
10614642	Not Issued	30	07/07/2003	Method and system of testing data retention of memory	DIXIT, CHARUTOSH
60194073	Not Issued	159	04/03/2000	Driver waveform modling using two ceffectives	DIXIT, CHARUTOSH
60450604	Not Issued	159	02/26/2003	Managing peak and average power consumption during data retention testing of memories	DIXIT, CHARUTOSH
09814417	6845348	150	03/21/2001	DRIVER WAVEFORM MODELING WITH MULTIPLE EFFECTIVE CAPACITANCES	DIXIT, CHARUTOSHI

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Last Name = SHEN
First Name = WILLIAM

Application#	Patent#	Status	Date Filed	Title	Inventor Name
10614642	Not Issued	30	07/07/2003	Method and system of testing data retention of memory	SHEN, WILLIAM
10767314	6888367	150	01/28/2004	METHOD AND APPARATUS FOR TESTING INTEGRATED CIRCUIT CORE MODULES	SHEN, WILLIAM
10975315	Not Issued	30	10/28/2004	Test clocking scheme	SHEN, WILLIAM
60450604	Not Issued	159	02/26/2003	Managing peak and average power consumption during data retention testing of memories	SHEN, WILLIAM
60104889	Not Issued	159	10/20/1998	ADDRESS WRAP FUNCTION FOR ADDRESSABLE SEMICONDUCTOR DEVICES	SHEN, WILLIAM S.
09796285	Not Issued	95	02/28/2001	MULTI-CYCLE SYMBOL LEVEL ERROR CORRECTION AND MEMORY SYSTEM	SHEN, WILLIAM W.
10171863	6667929	150	06/14/2002	POWER GOVERNOR FOR DYNAMIC RAM	SHEN, WILLIAM W.
10280315	Not Issued	161	10/25/2002	Volatilization of a drug from an inclusion complex	SHEN, WILLIAM W.
10861554	Not Issued	30	06/03/2004	Multiple dose condensation aerosol devices and methods of forming condensation aerosols	SHEN, WILLIAM W.
10996162	Not Issued	30	11/23/2004	Treatment of breakthrough pain by drug aerosol inhalation	SHEN, WILLIAM W.
60335049	Not Issued	159	10/30/2001	Volatilization of nicotine from an inclusion complex	SHEN, WILLIAM W.
60371457	Not Issued	159	04/09/2002	Volatilization of a drug from an inclusion complex	SHEN, WILLIAM W.
60530058	Not Issued	159	12/16/2003	Treatment of breakthrough pain by drug aerosol inhalation	SHEN, WILLIAM W.
07755209	5267242	250	09/05/1991	METHOD AND APPARATUS FOR SUBSTITUTING SPARE MEMORY CHIP FOR MALFUNCTIONING MEMORY CHIP WITH SCRUBBING	SHEN, WILLIAM W.
08085215	5479640	250	06/30/1993	SIMPLIFIED MEMORY ROW	SHEN, WILLIAM W.

				REDRIVE SYSTEM	
08260125	Not Issued	166	06/15/1994	BARCODE SCANNER FOR POOR OR LOW CONTRAST SURFACES	SHEN, WILLIAM W.
08350579	5581071	150	12/06/1994	BARCODE SCANNER WITH ADJUSTABLE LIGHT SOURCE INTENSITY	SHEN, WILLIAM W.
08414553	Not Issued	161	03/31/1995	MECHANISM FOR LOCKING A UNIT OF STORAGE IN A MULTIPROCESSOR SYSTEM	SHEN, WILLIAM W.
08452364	Not Issued	161	05/30/1995	MECHANISM FOR LOCKING A UNIT OF STORAGE IN A MULTIPROCESSOR SYSTEM	SHEN, WILLIAM W.
08570446	5691996	250	12/11/1995	MEMORY IMPLEMENTED ERROR DETECTION AND CORRECTION CODE WITH ADDRESS PARITY BITS	SHEN, WILLIAM W.
08570448	5768294	150	12/11/1995	MEMORY IMPLEMENTED ERROR DETECTION AND CORRECTION CODE CAPABLE OF DETECTING ERRORS IN FETCHING DATA FROM A WRONG ADDRESS	SHEN, WILLIAM W.
08599672	Not Issued	161	02/12/1996	BARCODE SCANNER FOR POOR OR LOW CONTRAST SURFACES	SHEN, WILLIAM W.
08765988	Not Issued	161	01/10/1997	SHARED CACHE MEMORY DEVICE	SHEN, WILLIAM W.
09325814	6480982	150	06/04/1999	COMPUTER RAM MEMORY SYSTEM WITH ENHANCED SCRUBBING AND SPARING	SHEN, WILLIAM W.
09326233	6386456	150	06/04/1999	MEMORY CARD IDENTIFICATION SYSTEM	SHEN, WILLIAM W.
09855240	6941414	150	05/15/2001	HIGH SPEED EMBEDDED DRAM WITH SRAM-LIKE INTERFACE	SHEN, WILLIAM WU
10072346	Not Issued	95	02/06/2002	ADDRESS WRAP FUNCTION FOR ADDRESSABLE MEMORY DEVICES	SHEN, WILLIAM WU
10460791	6674684	150	06/11/2003	MULTI-BANK CHIP COMPATIBLE WITH A CONTROLLER DESIGNED FOR A LESSER NUMBER OF BANKS AND METHOD OF OPERATING	SHEN, WILLIAM WU
07686721	5274646	250	04/17/1991	EXCESSIVE ERROR CORRECTION CONTROL	SHEN, WILLIAM WU
08570447	5761221	150	12/11/1995	MEMORY IMPLEMENTED ERROR DETECTION AND CORRECTION CODE USING MEMORY MODULES	SHEN, WILLIAM WU
08824098	5751745	150	03/25/1997	MEMORY IMPLEMENTED ERROR DETECTION AND CORRECTION CODE WITH ADDRESS PARITY BITS	SHEN, WILLIAM WU
09059114	6052772	150	04/13/1998	MEMORY REQUEST PROTOCOL METHOD	SHEN, WILLIAM WU

09059221	6182174	150	04/13/1998	MEMORY CARD INTERFACE METHOD	SHEN, WILLIAM WU
09070389	6163857	150	04/30/1998	COMPUTER SYSTEM UE RECOVERY LOGIC	SHEN, WILLIAM WU
09419594	Not Issued	164	10/18/1999	ADDRESS WRAP FUNCTION FOR ADDRESSABLE MEMORY DEVICES	SHEN, WILLIAM WU
09450548	6460157	150	11/30/1999	METHOD SYSTEM AND PROGRAM PRODUCTS FOR ERROR CORRECTION CODE CONVERSION	SHEN, WILLIAM WU
09451133	6463563	150	11/30/1999	SINGLE SYMBOL CORRECTION DOUBLE SYMBOL DETECTION CODE EMPLOYING A MODULAR H-MATRIX	SHEN, WILLIAM WU
09451261	6457154	150	11/30/1999	DETECTING ADDRESS FAULTS IN AN ECC-PROTECTED MEMORY	SHEN, WILLIAM WU
09452079	6519736	150	11/30/1999	GENERATING SPECIAL UNCORRECTABLE ERROR CODES FOR FAILURE ISOLATION	SHEN, WILLIAM WU
10457274	Not Issued	95	06/09/2003	LAYING HEAD FOR ROD ROLLING MILL	SHEN, WILLIAM X.
60389786	Not Issued	159	06/19/2002	Laying head for rod rolling mill	SHEN, WILLIAM X.
06370268	Not Issued	161	04/20/1982	APPARATUS FOR REGULATING ADMINISTRATION OF GAS TO A SUBJECT	SHENE, WILLIAM
06606981	4595019	150	05/04/1984	STONE DISINTEGRATOR	SHENE, WILLIAM R.
06666770	4620545	150	10/31/1984	NON-INVASIVE DESTRUCTION OF KIDNEY STONES	SHENE, WILLIAM R.
06772039	4606331	150	09/03/1985	ELECTRODE FOR FIBER OPTIC SCOPES	SHENE, WILLIAM R.
06847696	4696299	150	04/03/1986	NON-INVASIVE DESTRUCTION OF KIDNEY STONES	SHENE, WILLIAM R.
06852835	4763652	150	04/16/1986	AIMING SYSTEM FOR KIDNEY STONE DISINTEGRATOR	SHENE, WILLIAM R.
07001690	4737380	150	01/09/1987	ELECTRODE WITH STRETCHED HEAT-SHRINKABLE OUTER INSULATOR	SHENE, WILLIAM R.
07342809	4938210	150	04/25/1989	INHALATION CHAMBER IN VENTILATOR CIRCUIT	SHENE, WILLIAM R.
08153091	Not Issued	166	11/17/1993	PEAK FLOW METER	SHENE, WILLIAM R.

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08344530	5627324	150	11/23/1994	PEAK FLOW METER	SHENE, WILLIAM R.
08438156	5565630	150	05/11/1995	PEAK FLOW METER	SHENE, WILLIAM R.
07664048	Not Issued	89	02/07/1991	MODIFIED FUEL PROCESS LOADING SYSTEM	SHENEFELT, WILLIAM B.
07164855	4931656	150	03/07/1988	MEANS TO DYNAMICALLY DISCHARGE A CAPACITIVELY CHARGED ELECTRICAL DEVICE	SHENG, WILLIAM
07166433	Not Issued	161	03/10/1988	TEMPERATURE LIMITING MEANS	SHENG, WILLIAM
07316485	4912335	150	02/28/1989	MEANS FOR RAPID CHARGING AND DYNAMIC DISCHARGING OF A CAPACITIVELY CHARGED ELECTRICAL DEVICE	SHENG, WILLIAM
10768725	Not Issued	71	01/30/2004	Packaged power semiconductor device having a silicon nitride ceramic substrate with active brazed copper metallization	SHENG, WILLIAM
10771204	Not Issued	95	02/03/2004	SILICON NITRIDE INSULATING SUBSTRATE FOR POWER SEMICONDUCTOR MODULE	SHENG, WILLIAM W.
60443786	Not Issued	159	01/30/2003	Silicon nitride ceramic substrate with active brazed copper metallization for power semiconductor "TO" packages	SHENG, WILLIAM W.
60443787	Not Issued	159	01/30/2003	Silicon nitride ceramic substrate with integrated heat sink for power semiconductors	SHENG, WILLIAM W.
60607862	Not Issued	159	09/08/2004	Solder-bumped power semiconductor module	SHENG, WILLIAM W.
06531310	D279182	150	09/12/1983	FRONT PANEL FOR A GRAPHIC EQUALIZER OR SIMILAR ARTICLE	SHENK, WILLIAM B.
06373062	4535404	150	04/29/1982	METHOD AND APPARATUS FOR ADDRESSING A PERIPHERAL INTERFACE BY MAPPING INTO MEMORY ADDRESS SPACE	SHENK, WILLIAM H.
06381999	4513392	150	05/25/1982	METHOD AND APPARATUS FOR	SHENK, WILLIAM H.

				GENERATING A REPETITIVE SERIAL PATTERN USING A RECIRCULATING SHIFT REGISTER	
06382000	4509118	150	05/25/1982	METHOD AND APPARATUS FOR DEFINING MAGNETIC DISK TRACK FIELD LENGTHS USING A PROGRAMMABLE COUNTER	SHENK, WILLIAM H.

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query-by-example search system which produces a list of patents that are
most closely related linguistically to the application searched. This
search was prepared by the staff of the Scientific and Technical
Information Center, SIRA.

5319395
5877742
5764581
6072185
6237122
6243348
4796260
5430861
5805155
5845292
5930518
6181609
4313160
4455483
4847842
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5321699
5386422
5388074
5469444
5481531
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5524235
5608892
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5797027
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5860111
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6163832
6178121
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4849974
4849976
4855903
4953121
5274782
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5477492
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5537577
5561671
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5664149
5742509
5781495
5809273
5818789